Abstracts

Status of InP HEMT Technology for Microwave Receiver Applications (1996 Vol. I [MWSYM])

P.M. Smith. "Status of InP HEMT Technology for Microwave Receiver Applications (1996 Vol. I [MWSYM])." 1996 MTT-S International Microwave Symposium Digest 96.1 (1996 Vol. I [MWSYM]): 5-8.

The current status of InP-based high electron mobility transistor (HEMT) technology for low noise amplification at frequencies up to more than 100 GHz is presented. Following a review of recent advances industry-wide in both device and circuit performance, two issues, which will pace the rate at which this new technology can be inserted into microwave systems material/process maturity and long-term reliability--are discussed.

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